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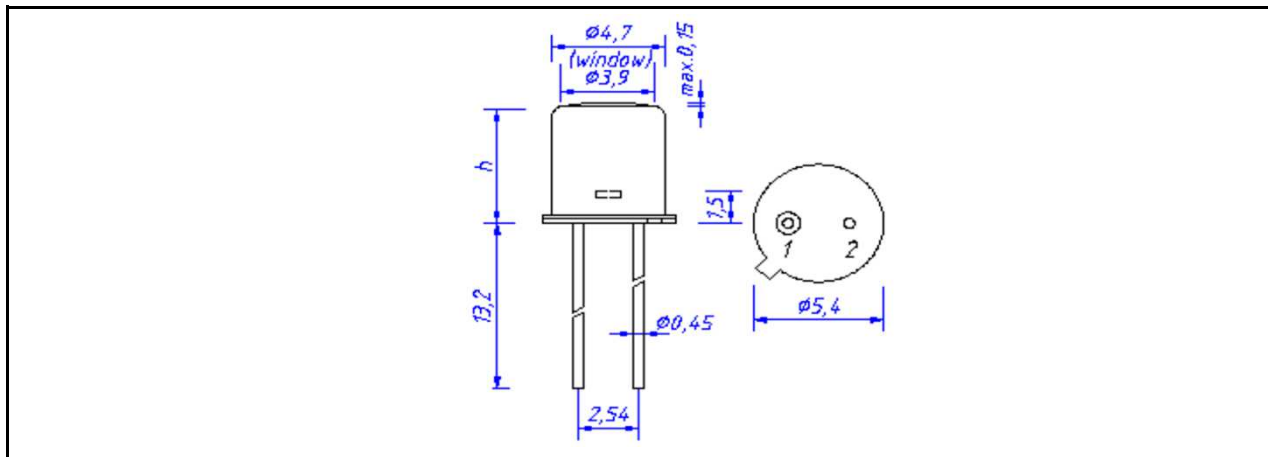
Data Sheet

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UV photodiode
EOPD-280-0-0.3-1

Rev. 06, 2017

Radiation	Type	Technology	Case
ultraviolet	UV-glass	SiC	TO-52


 1 - anode, 2 - cathode + case, $h=3.7$ mm

Description:

Highly reliable low cost SiC photodiode with high spectral sensitivity in the UV range (210 nm - 355 nm), mounted in hermetically sealed TO-52 package with UV-glass window

Characteristics:

- ◆ optional with insulated mounting of the photodiode
- ◆ high temperature option for operating up to 150°C
- ◆ RoHS and WEE compliant

Applications:

- ◆ universal measurements in the UV range
- ◆ sterilization lamp monitoring
- ◆ flame monitoring

Maximum Ratings
 $T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Active area size	A	0.365 x 0.365	mm ²
Active area	A	0.1	mm ²
Reverse voltage	V_R	20	V
Operating temperature range	T_{amb}	-40 to +125	°C
Storage temperature range	T_{stg}	-40 to +125	°C
Soldering temperature, 3 s	T_{sol}	260	°C



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UV photodiode

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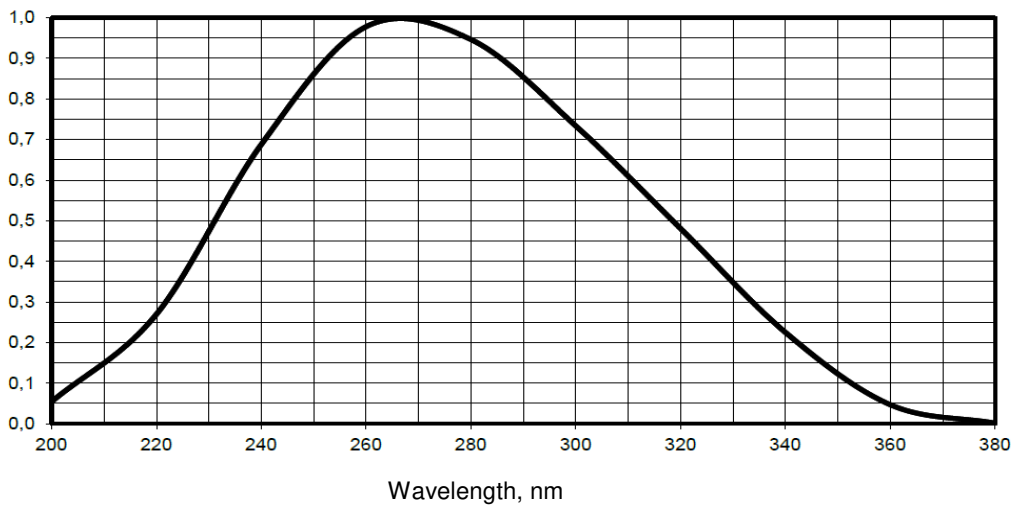
Rev. 06, 2017

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Dark current	$V_R = 1\text{ V}$	I_D		10		fA
Peak sensitivity wavelength	$V_R = 0\text{ V}$	λ_p		265		nm
Responsivity at λ_p	$V_R = 0\text{ V}$	S_λ		0.18		A/W
Responsivity at $\lambda = 254\text{ nm}$	$V_R = 0\text{ V}$	S_λ		0.16		A/W
Sensitivity range at $0.1 S_{max}$	$V_R = 0\text{ V}$	$\lambda_{min}; \lambda_{max}$	210		355	nm
Junction capacitance	$V_R = 0\text{ V}$	C_J		30		pF
Acceptance angle	$V_R = 0\text{ V}$	ϕ		± 40		deg

Relative spectral sensitivity



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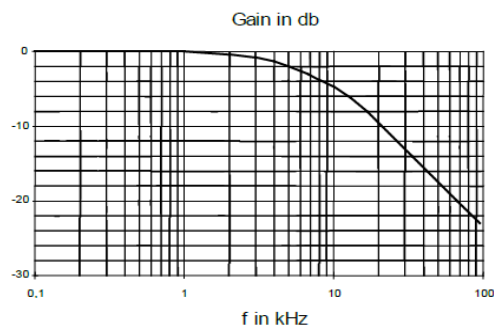
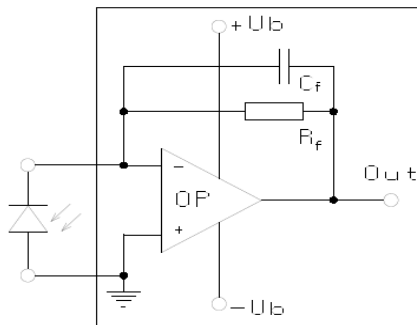
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UV photodiode

EOPD-280-0-0.3-1

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Rev. 06, 2017

application example



The application example shows a typical circuit R_f is responsible for the gain of the circuit C_f compensates the reverse junction capacitance of the photodiode and the input capacitance of the OP-amp. The exact value of C_f depends on R_f , used OP-amp and capacitance of the circuit. A typical value is 1pF.

The chart shows dependence of amplitude of the application circuit with OP-amp = AD795, $R_f = 10 \text{ M}\Omega$ and $C_f = 1 \text{ pF}$.

Art. Nr. 141 005



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Data Sheet

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Selective photodiode

EOPD-525-1-0.9-1

Rev. 02, 2017

Wavelength range	Type	Case
green	GaP	SMD 3216

Description:	
<p>Unit: mm Tolerance: $\pm 0,1$</p> <p>All sizes in mm</p>	
Applications:	
<p>Alarm systems, light barriers, daylight sensors, for nearly Vλ matched detectors.</p>	

Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Active area	A	0.73	mm ²
Temperature coefficient of I_D	TC(I_D)	5	%/K
Temperature coefficient of I_{PH}	TC(I_{PH})	0.25	%/K
Temperature coefficient of λ_C	TC(λ_C)	0.15	nm/K
Operating temperature range	T_{amb}	-20 to +85	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-40 to +100	$^{\circ}\text{C}$



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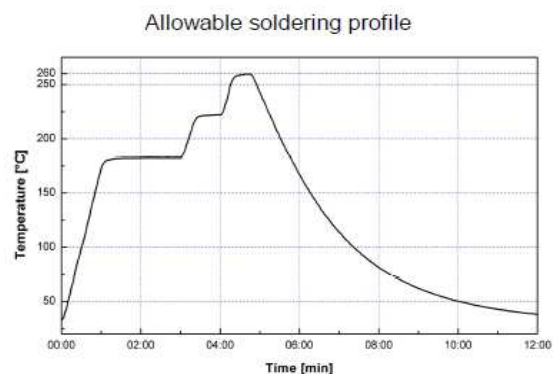
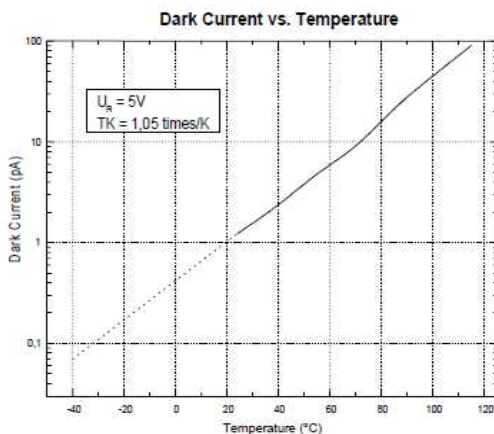
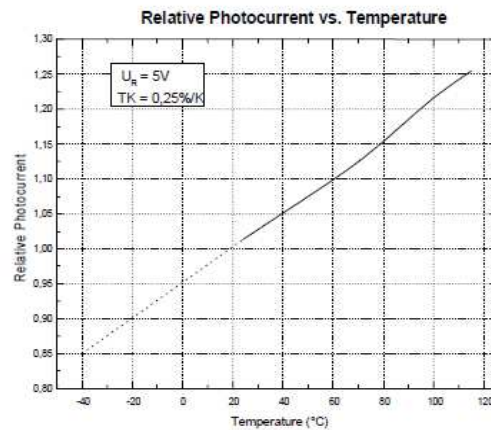
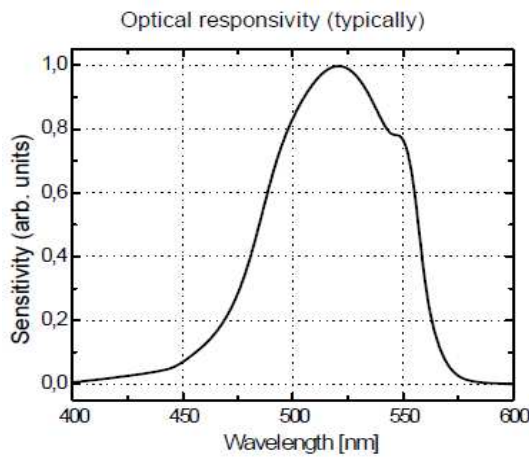
Selective photodiode

EOPD-525-1-0.9-1

Optical and Electrical Characteristics

T_{amb}= 23°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Dark current	V _R =5 V	I _D		5	30	pA
Peak sensitivity wavelength	V _R =0 V	λ _p		525		nm
Responsivity at λ _p	V _R =0 V	S _λ		0.3		A/W
Sensitivity range at 1%	V _R =0 V	λ _{min} , λ _{max}	410		580	nm
Spectral bandwidth at 50%	V _R =0 V	Δλ _{0,5}		70		nm
Junction capacitance	V _R =0 V	C _J		100		pF
Switching times (R _L =50 Ω)	V _R =1 V	t _r ; t _f		35		ns



Art. No. 142 005



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Selective photodiode

EOPD-525-1-0.9-2

Rev. 02, 2017

Wavelength range	Type	Case
green	GaP	SMD 3216 with lens

	Description: Narrow bandwidth and high spectral sensitivity in the green visible range (500...600 nm), compact design in SMD package with lens allows for easy circuit board mounting and assembling of arrays.
	Applications Alarm systems, light barriers, daylight sensors, for nearly V_{λ} matched detectors.

All sizes in mm

Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Active area	A	0.73	mm^2
Temperature coefficient of I_D	$TC(I_D)$	4.7	%/K
Temperature coefficient of I_{PH}	$TC(I_{PH})$	0.25	%/K
Temperature coefficient of λ_C	$TC(\lambda_C)$	0.15	nm/K
Operating temperature range	T_{amb}	-40 to +85	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-40 to +100	$^{\circ}\text{C}$

Optical and Electrical Characteristics

$T_{amb} = 23^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Dark current	$V_R = 5\text{ V}$	I_D		5	30	pA
Peak sensitivity wavelength	$V_R = 0\text{ V}$	λ_p		525		nm
Responsivity at λ_p	$V_R = 0\text{ V}$	S_{λ}	0.15	0.3		A/W
Sensitivity range at 1%	$V_R = 0\text{ V}$	$\lambda_{min}, \lambda_{max}$	410		580	nm
Spectral bandwidth at 50%	$V_R = 0\text{ V}$	$\Delta\lambda_{0.5}$		70		nm
Junction capacitance	$V_R = 0\text{ V}$	C_J		100		pF
Switching times ($R_L = 50\ \Omega$)	$V_R = 1\text{ V}$	$t_r; t_f$		35		ns



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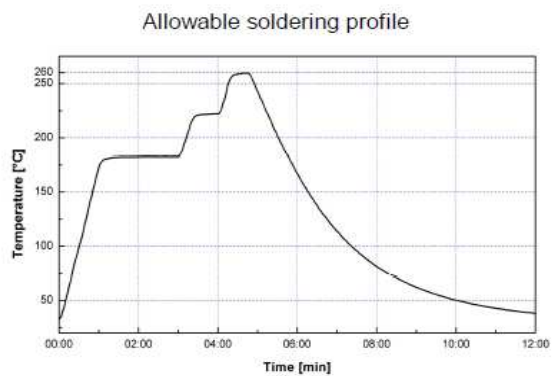
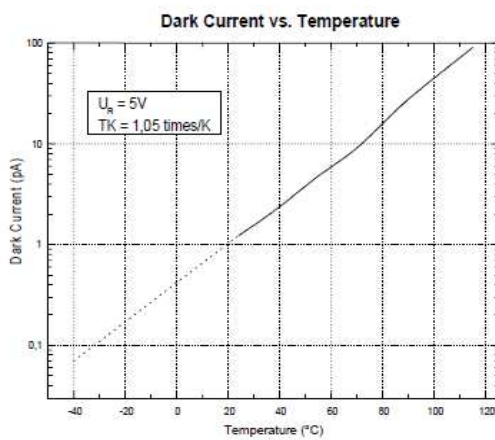
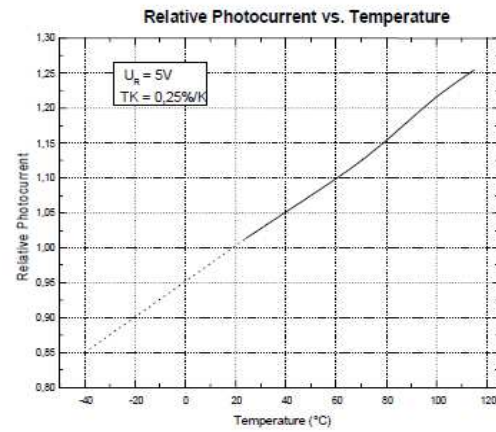
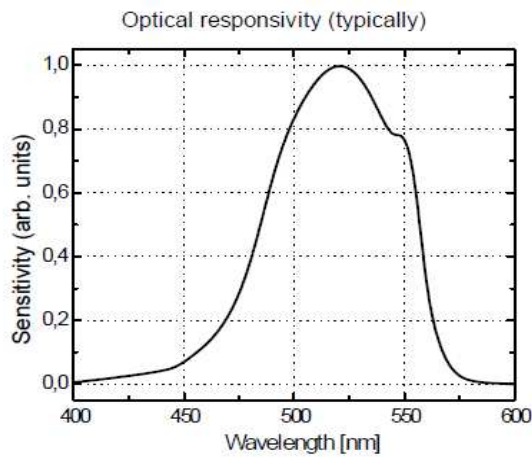
Data Sheet

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Selective photodiode

EOPD-525-1-0.9-2

Rev. 02, 2017



Art. No. 142 010



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customized optoelectronics



Product Data Sheet

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PD IR

EOPD-880-0-0.5

Rev. 01 aus 2011

Radiation	Type	Case
infrared		TO46 with lens

Description:	
	<p>Selective photodiode mounted in hermetically sealed TO-46 package. Narrow bandwidth and high spectral sensitivity in the infrared range (810 ... 950 nm)</p> <p>Applications alarm systems, light barriers, spectral sensors, optical communication</p>

Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Active area/ Effective active area	A / A_{eff}	0.17	mm^2
Temperature coefficient of I_D	$T_C(I_D)$	5	%/ K
Temperature coefficient of S_{λ} at λ_p	$T_C(S_{\lambda})$	0.25	%/ K
Operating temperature range	T_{amb}	-30 to +100	$^{\circ}\text{C}$
Soldering temperature ($t \leq 3\text{s}$, 3mm from case)	T_{sld}	260	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-40 to +125	$^{\circ}\text{C}$
Acceptance angle at 50% S_{λ}	φ	6	deg.

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Breakdown voltage ¹⁾	$I_R = 10\mu\text{A}$	V_R	5			V
Dark current	$V_R = 1\text{V}$	I_D		1.0	2.5	nA
Responsivity at λ_p	$V_R = 0\text{V}$	S_{λ}		0.3		A/W
Peak sensitivity wavelength ¹⁾	$V_R = 0\text{V}$	λ_p		890		nm
Sensitivity range at 10%	$V_R = 0\text{V}$	$\lambda_{min}, \lambda_{max}$	800		960	nm
Spectral bandwidth at 50%	$V_R = 0\text{V}$	$\Delta\lambda_{0.5}$		115		nm
Noise equivalent power	$\lambda = 880\text{ nm}$	NEP		8×10^{-15}		$\text{WHz}^{1/2}$
Dark resistance	$V_R = 10\text{ mV}$	R_D	20	100		G Ω
Switching time ($R_L = 50\ \Omega$)	$V_R = 1\text{V}$	t_r, t_f		170		ns
Junction capacitance	$V_R = 1\text{V}$	C_J		75		pF

¹⁾ for information only

Note: All measurements carried out with EPIGAP equipment

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Product Data Sheet

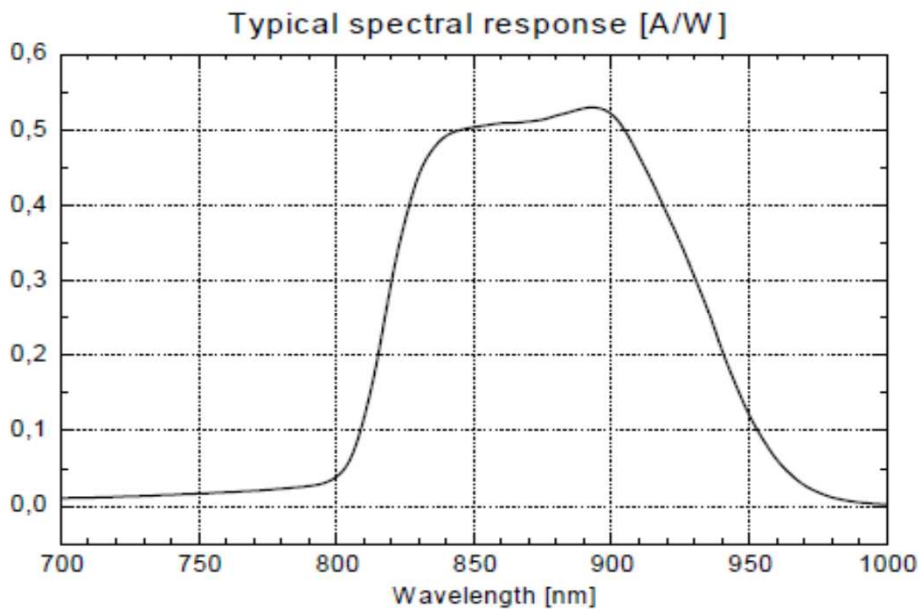
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PD IR **EOPD-880-0-0.5**

Rev. 01 aus 2011

Labeling

Type	Lot N°	I _p at 1V (typ.) [pA]	Quantity
EOPD-880-0-0.5			



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Data Sheet

Si Photodiode

EOPD-940-0-2.52

Spectral range	Type	Case
UV ... infrared	Si	TO-5, glass window cap

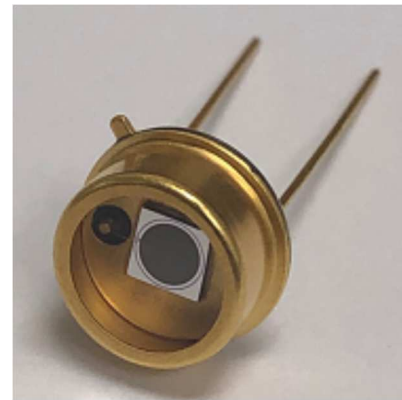
Circular (Ø2.52) 5 mm² active area photodiode in a hermetic TO-5 metal can. It is well suited for applications requiring visible and near infrared (NIR) light detection.

Features:

- > Wide dynamic range
- > High shunt resistance
- > Ultra low noise
- > Broadband spectral coverage

Applications:

- > Colorimeters
- > Photometers
- > Spectroscopy equipment
- > Fluorescence



Absolute maximum ratings

Parameters	Symbol	Rating	Unit
Reverse voltage	V _R	50	V
Operating temperature range	T _{OPR}	-40...+100	°C
Storage temperature range	T _{STG}	-55...+125	°C
Lead soldering temperature*	T _{LS}	260	°C

*Time 5 sec max, position: up to 3 mm from the body



Electro-optical characteristics:

T_{amb}= 25°C, unless otherwise specified

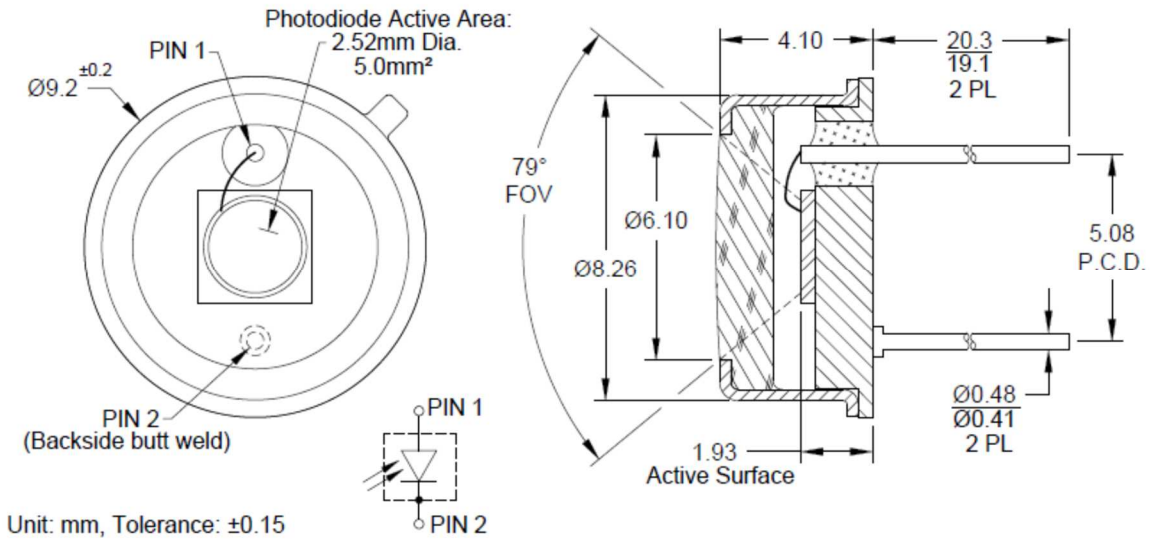
Parameters	Symbol	Min	Typ	Max	Unit	Test conditions
Dark current	I _D		0.1	1	nA	V _R =5 V
Breakdown voltage	V _{BR}	50			V	I _R =10 µA
Sensitivity range	λ	350		1100	nm	
Peak sensitivity WL	λ _P		950		nm	
Responsivity	S _λ		0.38		A/W	V _R =0 V, λ=633 nm
Responsivity	S _λ		0.55		A/W	V _R =0 V, λ=940 nm
Response time	t _R		30		ns	V _R =5 V, R _L =50 Ω, λ=635 nm
Junction capacitance	C _j		90		pF	V _R =0 V, 1 MHz
Junction capacitance	C _j		20	25	pF	V _R =5 V, 1 MHz
Shunt resistance	R _S	500	1000		MΩ	V _R =10 mV

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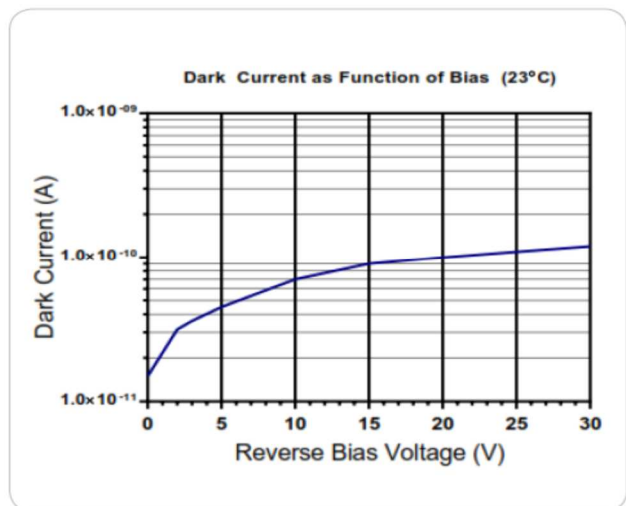
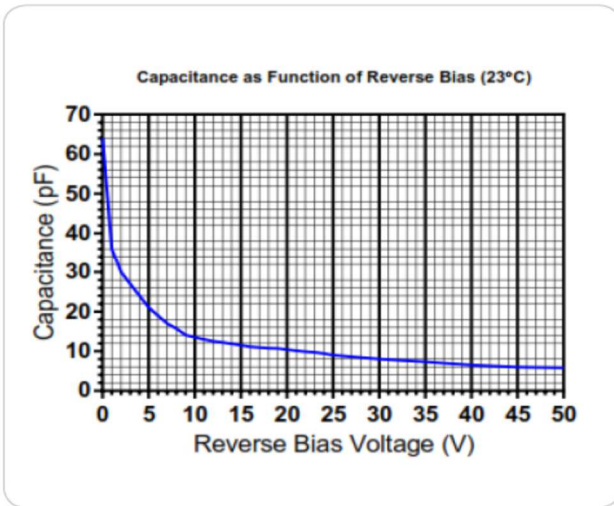
Data Sheet

Si Photodiode

EOPD-940-0-2.52



TO-5 package dimensions (2 pin)



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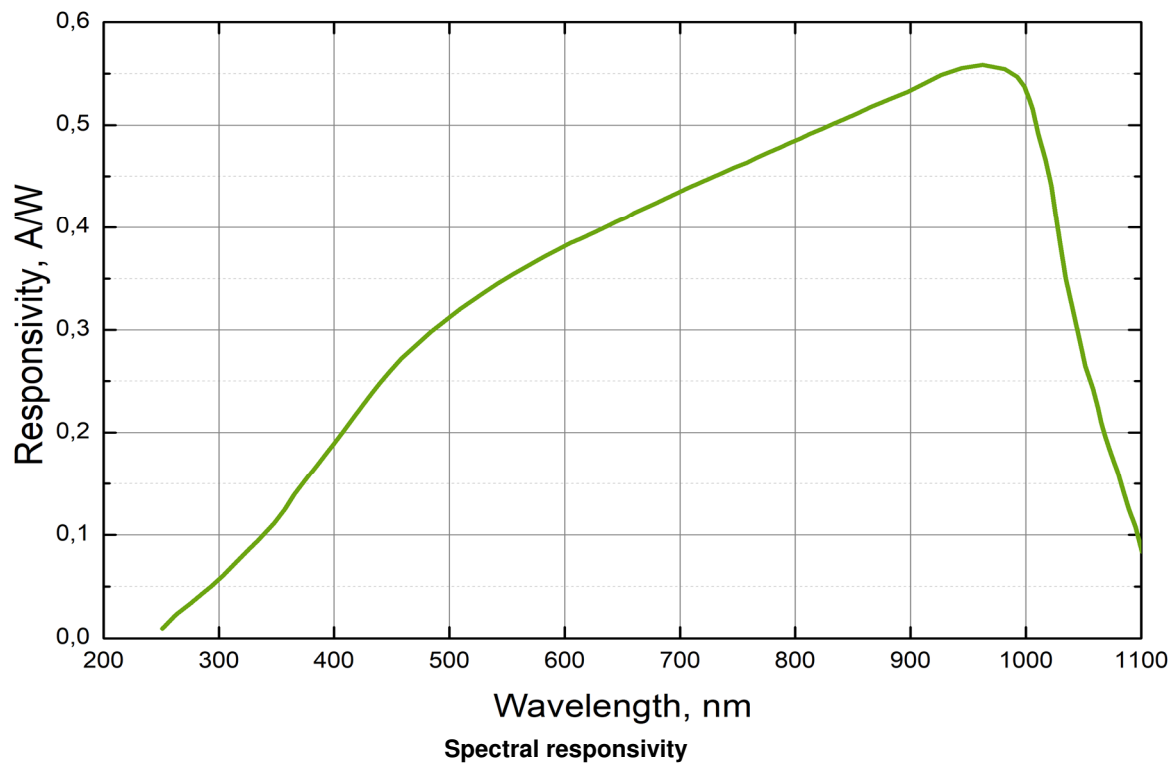
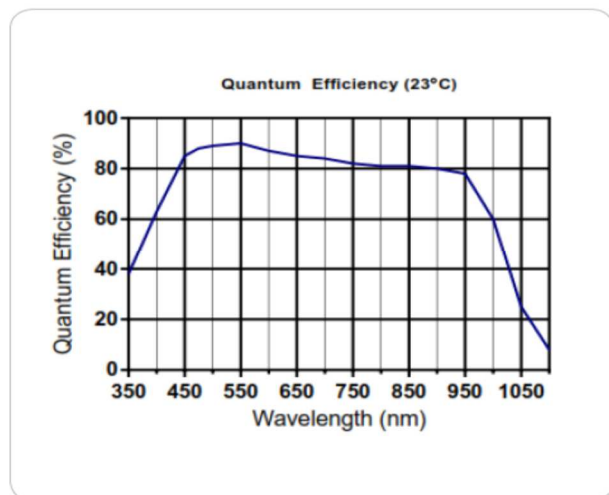
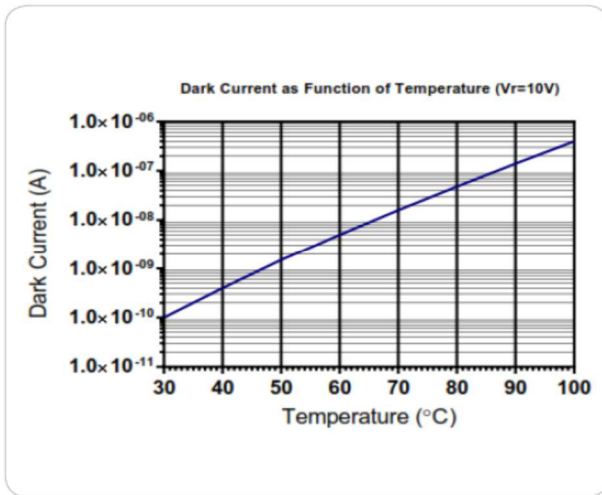
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Si Photodiode

EOPD-940-0-2.52

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Rev. 03, 2020



Art. No. 143 044



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